



《风光欣》技术资料

2SD882

NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY POWER AMPLIFIER

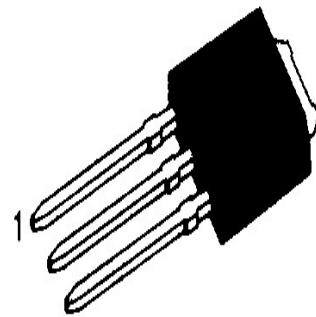
LOW SPEED SWITCHING

*Complement to 2SB772

ABSOLUTE MAXIMUM RATINGS(Ta=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I _c	3	A
Base Current (DC)	I _B	0.6	A
Collector Dissipation (T _c =25)	P _c	10	W
Collector Dissipation (T _a =25)	P _c	1	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	

TO-251



1. Base 1.2. Collector 3. Emitter

ELECTRICAL CHARACTERISTICS(Ta=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I _{CB0}	V _{CB} = 30V, I _E =0			1	μ A
Emitter-Cutoff Current	I _{EBO}	V _{EB} = 3V, I _c =0			1	μ A
*DC Current Gain	h _{FE1}	V _{CE} = 2V, I _c = 20mA	30	150		
	h _{FE2}	V _{CE} = 2V, I _c = 1A	60	160	400	
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 2A, I _B = 0.2A		0.3	0.5	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _c = 2A, I _B = 0.2A		1.0	2.0	V
Current Gain-Bandwidth Product	f _T	V _{CE} = 5V, I _E =0.1A		90		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V, I _E =0, f=1MHZ		45.0		pF

*Pulse Test :PW <350uS, Duty Cycle <2%

HFE (2) CLASSIFICATION

Classification	R	Q	P	I
HFE(2)	60-120	100-200	160-320	200-400